

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
MI22-1724SERIAL NO.  
UnknownLIST OF ART CITED BY APPLICANT  
(Use several sheets if necessary)APPLICANT  
Cem Basceri et al.FILING DATE  
Filed HerewithGROUP  
Unknown

## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA			Cem Basceri et al. (as filed)			Filed Concurrently
EF	AB	09/476,516		Cem Basceri (as filed and as amended)			01/03/00
EF	AC	09/580,733		Cem Basceri (as filed)			05/26/00
EF	AD	5,459,635	10/17/95	Tomozawa et al.	361	321.5	
EF	AE	5,618,761	04/08/97	Eguchi et al.	438	785	
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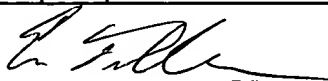
## FOREIGN PATENT DOCUMENTS

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12/06/01

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Form PTO-1449

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09/905,286

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APPLICANT  
Cem Basceri et al.

FILING DATE  
July 13, 2001

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Unknown

U.S. PATENT DOCUMENTS

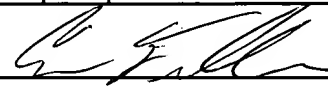
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EF	AA	5,256,455	10/26/93	Numasawa			
EF	AB	5,731,948	01/21/97	Endo			
EF	AC	5,776,254	03/24/98	Yializis et al.			
EF	AD	5,783,253	07/07/98	Yuuki et al.			
EF	AE	5,798,903	07/21/98	Roh			
EF	AF	6,043,526	08/25/98	Dhote et al.			
EF	AG	6,046,345	03/28/00	Ochiai			
EF	AH	6,078,492	04/04/00	Kadokura et al.			
EF	AI	6,153,898	06/20/00	Huang et al.			
EF	AJ	6,037,205	11/28/00	Watanabe			
EF	AK	6,037,205	03/14/00	Huh et al.			

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		Document Number	Date	Country	Class	Subclass	Translation	
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EF	AL	0 855 735 A2	26.01.98	EPO - Zhao et al.; Applied Materials, Inc.				
EF	AM	0 957 522 A2	12.05.99	EPO - Ueda, Michihito; Matsushita Electric Ind. Co.,				
EF	AN	WO 98/39497	20.02.98	WIPO - Simpson, John et al.				
EF	AO	0 474 140 A1	30.08.91	EPO - Kamiyama, Satoshi c/o NEC Corporation				
EF	AP	WO 99/64645	11.06.99	WIPO - Narwankar et al.; Applied Materials, Inc;				

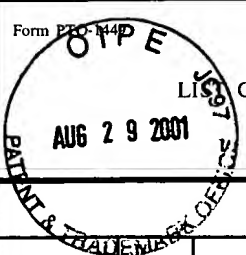
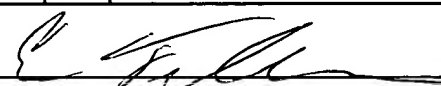
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

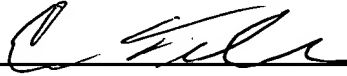
EF	AR	Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD Ba,Sr,TiO<sub>3</sub></i> , pp. 1-21 (MRS Fall Meeting 12/01/94).
EF	AS	Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 pages.
EF	AT	Y-C Choi et al., Abstract, <i>Improvements of the Properties of Chemical-Vapor-Deposited (Ba,Sr)TiO<sub>3</sub> Films Through Use of a Seed Layer</i> , 36 JPN. J. APPL. PHYS. Pt. 1, No. 11, pp. 6824-6828 (1997)

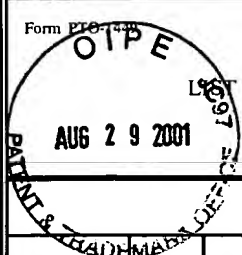

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Cem Basceri et al.		GROUP Unknown	
				FILING DATE July 13, 2001			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
EF	AA	5/470,398	11/28/95 Shibuya et al.				
EF	AB	5/254,505	10/19/93 Kamiyama				
EF	AC	6,156,638	12/05/00 Agarwal et al.				
EF	AD	6,165,834	12/26/00 Agarwal et al.				
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EF	AR	Chung Ming Chu et al., Abstract, <i>Electrical properties and crystal structure of (Ba,Sr)TiO<sub>3</sub> films prepared at low temperatures</i>					
		on a LaNiO <sub>3</sub> electrode by radio-frequency magnetron ..., 70 APPLIED PHYSICS LETTERS No. 2, pp. 249-251 (1997).					
EF	AS	Kazuhiro Eguchi et al., Abstract, <i>Chemical vapor deposition of (Ba,Sr)TiO<sub>3</sub> thin films for application in gigabit scale</i>					
		dynamic random access memories, 14 INTEGRATED FERROELECTRICS Nos. 1-4, Pt. 1, pp. 33-42 (1997).					
EF	AT	Q.X. Jia et al., Abstract, <i>Structural and dielectric properties of Ba<sub>0.5</sub>Sr<sub>0.5</sub> thin films with an epi-RuO<sub>2</sub> bottom electrode,</i>					
		19 INTEGRATED FERROELECTRICS Nos. 1-4, pp. 111-119 (1998).					
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EF	AR	Takaaki Kawahara et al., (Ba, Sr)TiO <sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes, 35 JPN. J. APPL. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).				
		Applications, Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.				
EF	AS	Rajesh Khamankar et al., A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM				
		Applications, Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.				
EF	AT	Yong Tae Kim et al., Abstract, Advantages of RuO <sub>4</sub> bottom electrode in the dielectric and leakage characteristics of (Ba,Sr)TiO <sub>3</sub> capacitor, 35 JPN. J. APPL. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).				
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Form PTO-1530 <div style="text-align: center;">  </div>		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1724		SERIAL NO. 09/905,286		
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EF	AR		S.H. Paek et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering</i> .					
			Ferroelectric Thin Films V. Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995).					
EF	AS		N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba<sub>0.99</sub>Sr<sub>0.01</sub>TiO<sub>3</sub></i> , 98 NIPPON					
			SERAMIKKUSU KYOKAI GAKUJUTSU RONBUNSHI No. 8, pp. 836-839 (1990).					
EF	AT		H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO<sub>3</sub>-BaTiO<sub>3</sub> thin films</i> , IEEE					
			International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992).					
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Form PTO 1449 <div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; text-align: center;"> <b>OPEN</b>  <b>AUG 29 2001</b>  <b>PATENT &amp; TRADEMARK OFFICE</b> </div>		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1724		SERIAL NO. 09/905,286	
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EF	AR	S. Yamamichi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba<sub>0.5</sub>)Sr<sub>0.5</sub>TiO<sub>3</sub> thin films prepared by ion beam sputtering</i> , 64 APPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994).					
EF	AS	M. Yamamuka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr)TiO<sub>3</sub> Thin-Films Prepared by Chemical-Vapor-Deposition</i> , 35 JPN. J. OF APPL. PHYS. Pt. 1, No. 2A, pp. 729-735 (1996).					
EF	AT	Arai T., et al.: <i>Preparation of SrTiO<sub>3</sub> Films on 8-Inch Wafers by Chemical Vapor Deposition</i> , Jap. Journal of Applied Physics, Vol. 35, No. 9B, Part 01, 09/01/96, Pgs. 4875-4879					
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Form PTO-1019 <div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; transform: rotate(-15deg);">           OFFICE            AUG 29 2001         </div>		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1724		SERIAL NO. 09/905,286	
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EF	AR		Kim, et al.: <i>Structural and Electrical Properties of BaTiO<sub>3</sub> grown on p-InP (100) by low-pressure metalorganic chemical vapor deposition at low temperature</i> , Applied Physics Letters, US, American Institute of Physics Vol. 65, No. 15, 10/10/94, Pgs. 1955-1957.				
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